



USS306PX

Preliminary

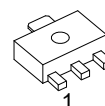
PNP SILICON TRANSISTOR

-3.7A, -100V PNP LOW $V_{CE(SAT)}$ TRANSISTOR

DESCRIPTION

The UTC **USS306PX** is PNP low $V_{CE(SAT)}$ transistor in a medium power and flat lead SOT-89 Surface-Mounted Device (SMD) plastic package.

NPN complement: USS306NX.

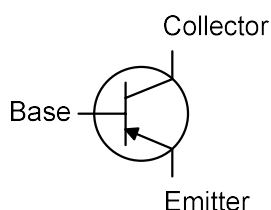


SOT-89

FEATURES

- * Very low collector-emitter saturation voltage $V_{CE(SAT)}$
- * High collector current capability I_C and I_{CM}
- * High collector current gain (h_{FE}) at high I_C
- * High energy efficiency due to less heat generation

EQUIVALENT CIRCUIT



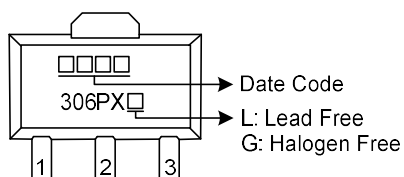
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
USS306PXL-AB3-R	USS306PXG-AB3-R	SOT-89	B	E	C	Tube

Note: Pin Assignment: B: Base E: Emitter C: Collector

USS306PXG-AB3-R	(1)Packing Type	(1) R: Tape Reel
	(2)Package Type	(2) AB3: SOT-89
	(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

MARKING



■ **ABSOLUTE MAXIMUM RATING** ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-3.7	A
Peak Collector Current	I_{CM}	-7.4	A
Power Dissipation	P_C	600	mW
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **THERMAL DATA**

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	208	$^{\circ}\text{C/W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ **ELECTRICAL CHARACTERISTICS** ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-100\mu\text{A}$, $I_E=0\text{A}$	-100			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-1\text{mA}$, $I_B=0\text{A}$	-100			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-100\mu\text{A}$, $I_C=0\text{A}$	-5			V
Collector-Base Cut-off Current	I_{CBO}	$V_{CB}=-80\text{V}$, $I_E=0\text{A}$			-100	nA
Emitter-Base Cut-off Current	I_{EBO}	$V_{EB}=-5\text{V}$, $I_C=0\text{A}$			-100	nA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C=-1\text{A}$, $I_B=-100\text{mA}$			-0.9	V
		$I_C=-4\text{A}$, $I_B=-400\text{mA}$			-1.05	V
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	$V_{CE}=-2\text{V}$, $I_C=-2\text{A}$			-0.85	V
DC Current Gain	h_{FE}	$V_{CE}=-2\text{V}$, $I_C=-500\text{mA}$	200			
		$V_{CE}=-2\text{V}$, $I_C=-1\text{A}$	150			
		$V_{CE}=-2\text{V}$, $I_C=-2\text{A}$	100			
		$V_{CE}=-2\text{V}$, $I_C=-4\text{A}$	25			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C=-500\text{mA}$, $I_B=-50\text{mA}$			-65	mV
		$I_C=-1\text{A}$, $I_B=-50\text{mA}$			-130	mV
		$I_C=-4\text{A}$, $I_B=-400\text{mA}$			-300	mV

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